

FIG. 1

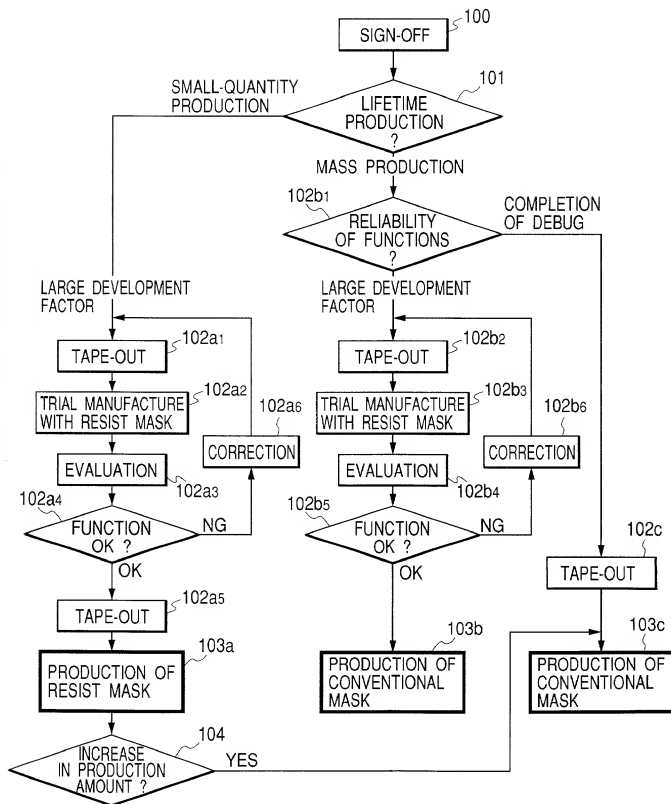


FIG. 2

MENU	EXCLUSIVE USE OF RESIST MASK	USE OF RESIST MASK FOR INITIAL PRODUCTION	USE OF RESIST MASK FOR DEVELOPMENT	EXCLUSIVE USE OF CONVENTIONAL MASK
TYPE	PRODUCTION OF ONLY RESIST MASK THROUGHOUT THIS FLOW	SMALL-QUANTITY PRODUCTION OF RESIST MASK, FOLLOWED BY MASS PRODUCTION OF CONVENTIONAL MASK	ONLY DEVELOPMENT OF RESIST MASK, FOLLOWED BY PRODUCTION OF CONVENTIONAL MASK AFTER DEBUG	PRODUCTION OF ONLY CONVENTIONAL MASK FROM THE BEGINNING
PRODUCTION AMOUNT	SMALL	SMALL → LARGE	LARGE	LARGE
DEVELOPMENT COST (FOR MASK)	SMALL	SMALL → LARGE	LARGE	MEDIUM~LARGE
DEVELOPMENT TAT	SHORT	SHORT	SHORT	LONG
POSSIBILITY OF PATTERN CHANGE	NOT ASKED	NOT ASKED	NOT ASKED	SMALL LARGE DEVELOPMENT COST IS NECESSARY UPON PATTERN CHANGE

FIG. 3

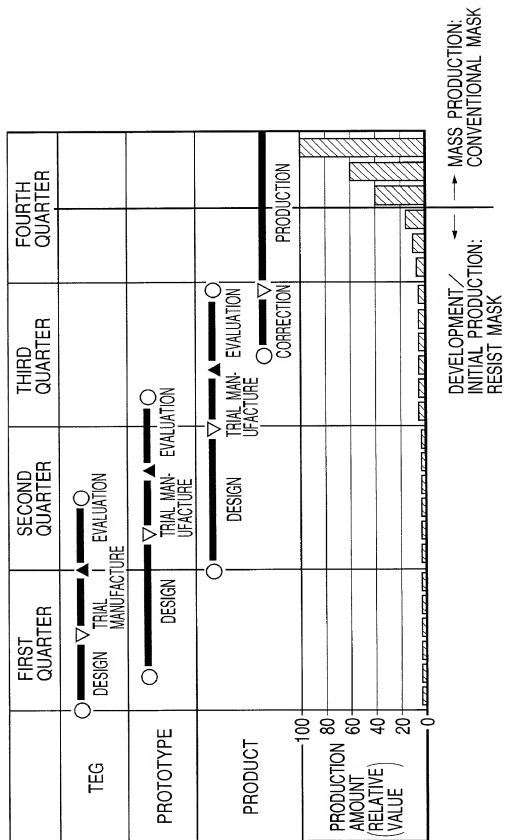


FIG. 4

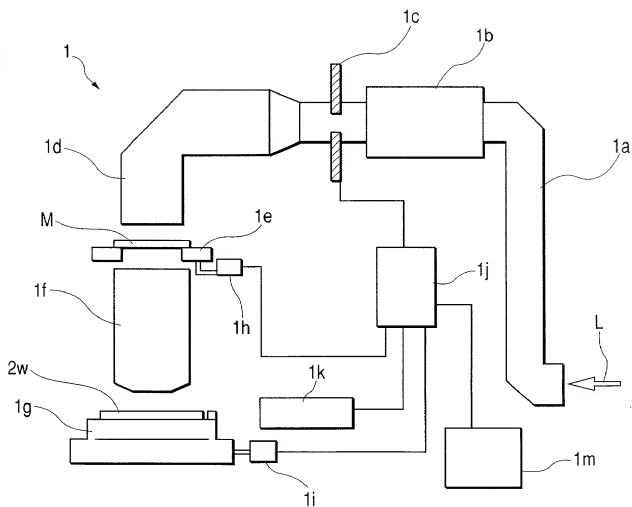


FIG. 5(a)

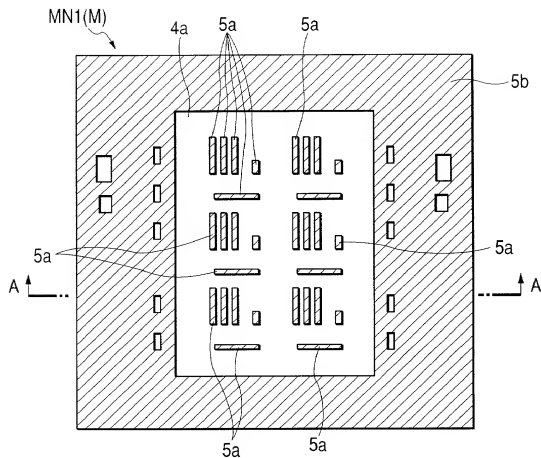


FIG. 5(b)

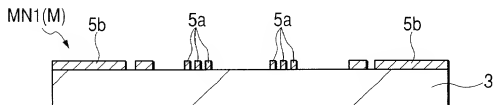


FIG. 6(a)

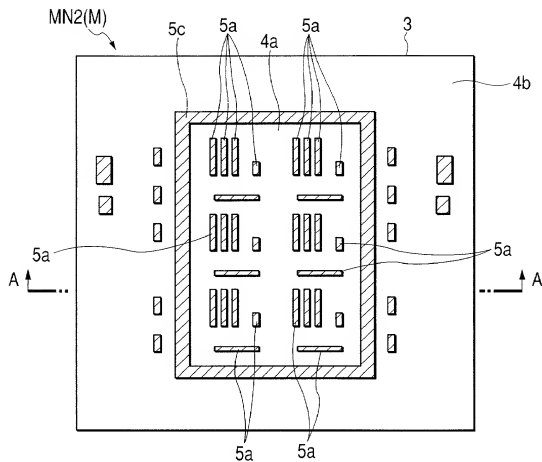


FIG. 6(b)

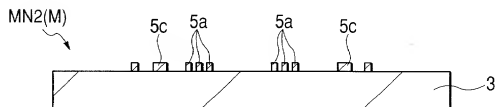


FIG. 7(a)

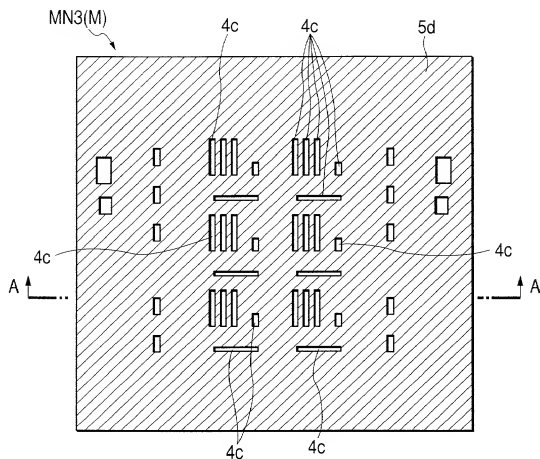


FIG. 7(b)

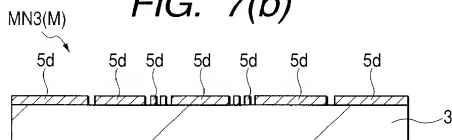


FIG. 8(a)

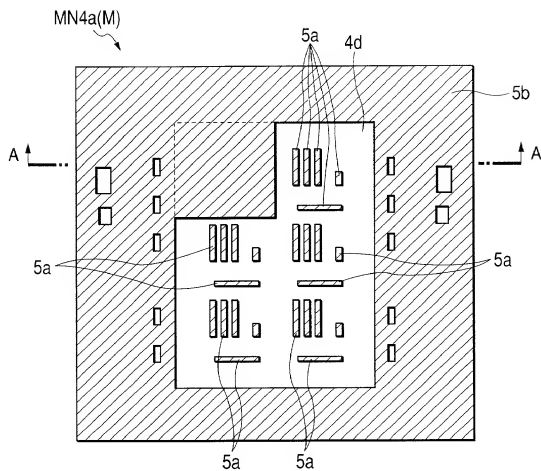


FIG. 8(b)

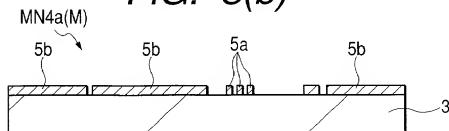




FIG. 9(a)

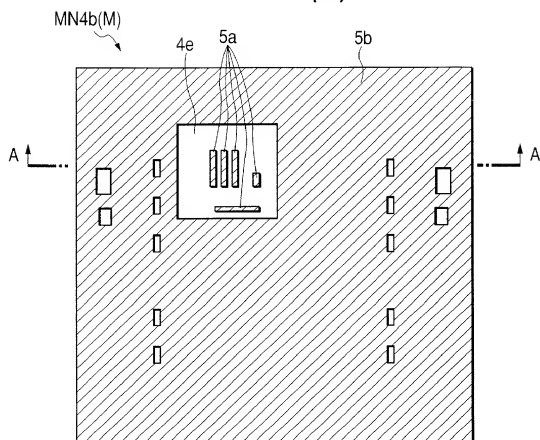


FIG. 9(b)

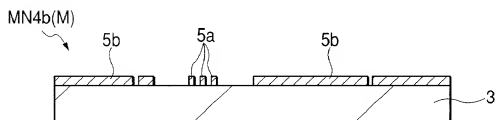


FIG. 10(a)

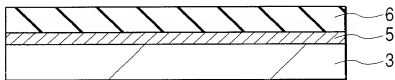


FIG. 10(b)

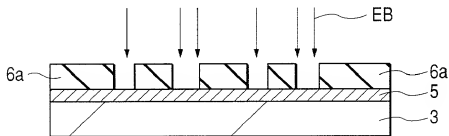


FIG. 10(c)

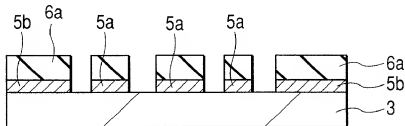


FIG. 10(d)

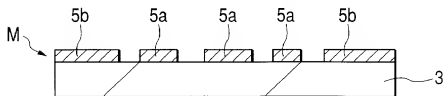


FIG. 11(a)

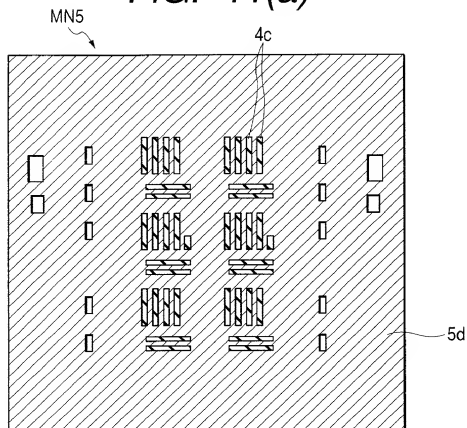


FIG. 11(b)

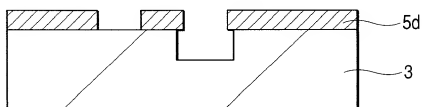
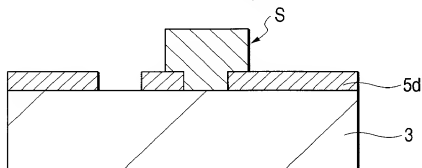


FIG. 11(c)



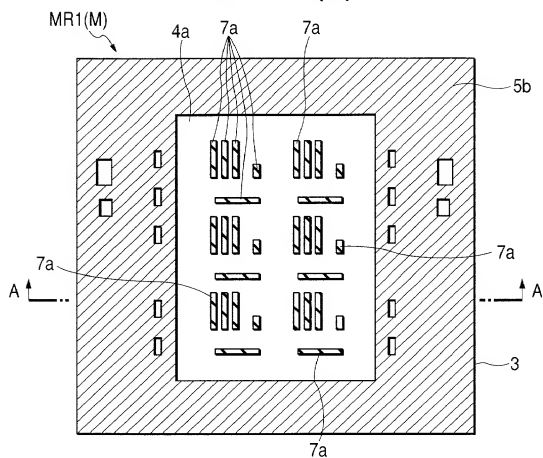
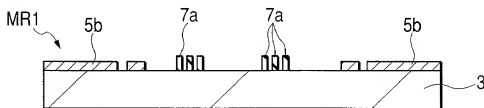
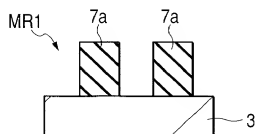
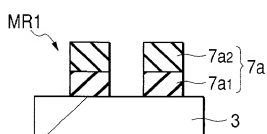
**FIG. 12(a)****FIG. 12(b)****FIG. 12(c)****FIG. 12(d)**

FIG. 13(a)

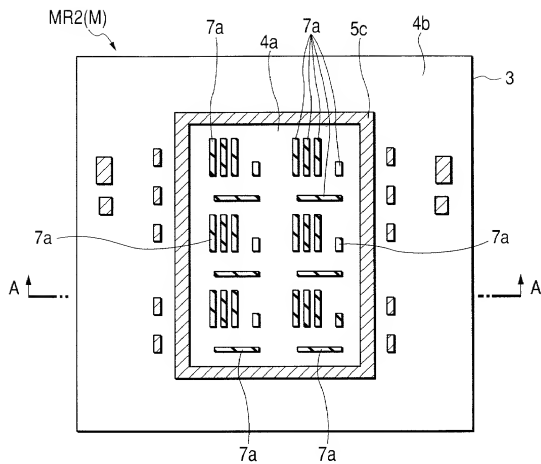


FIG. 13(b)

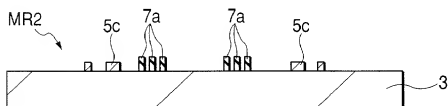


FIG. 14(a)

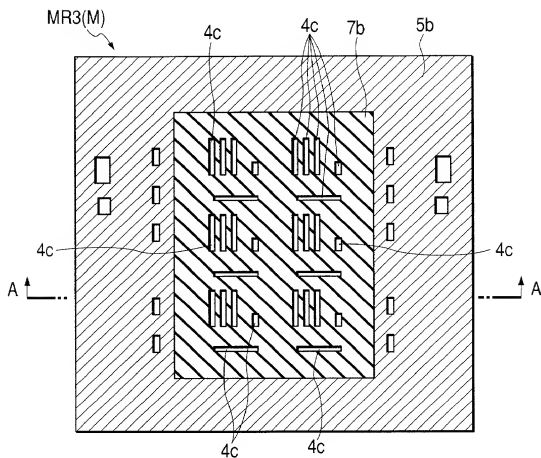
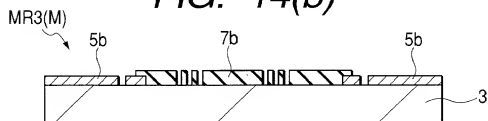
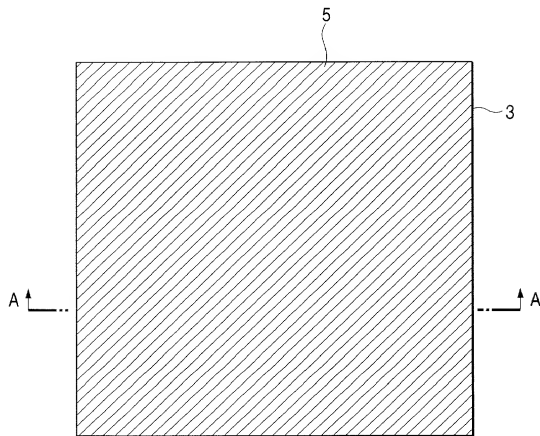


FIG. 14(b)



*FIG. 15(a)**FIG. 15(b)*

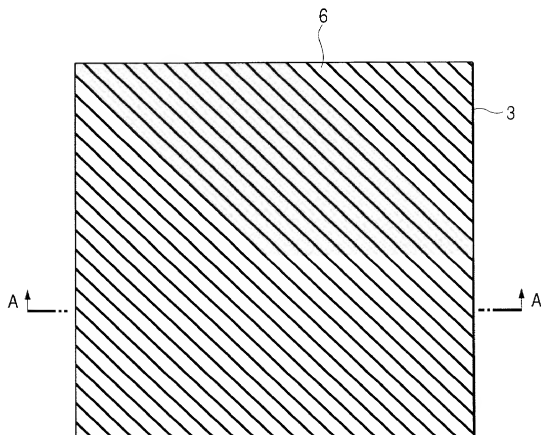
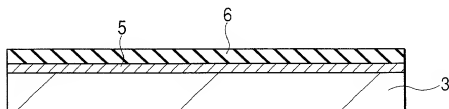
*FIG. 16(a)**FIG. 16(b)*



FIG. 17(a)

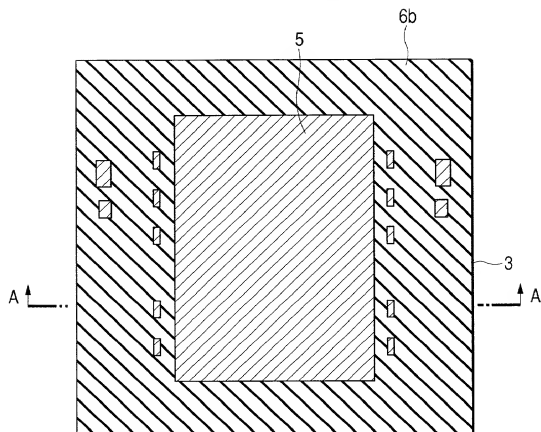
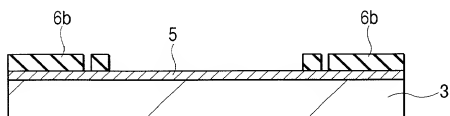


FIG. 17(b)



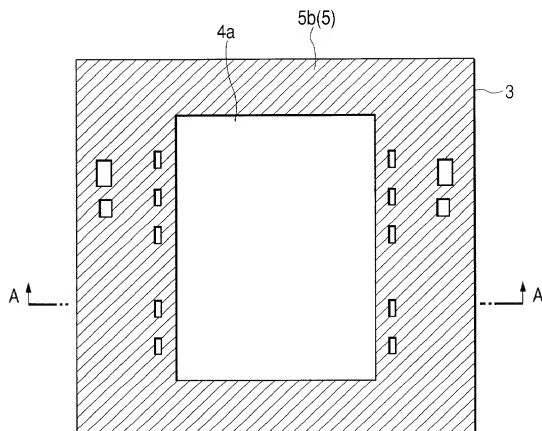
*FIG. 18(a)**FIG. 18(b)*

FIG. 19(a)

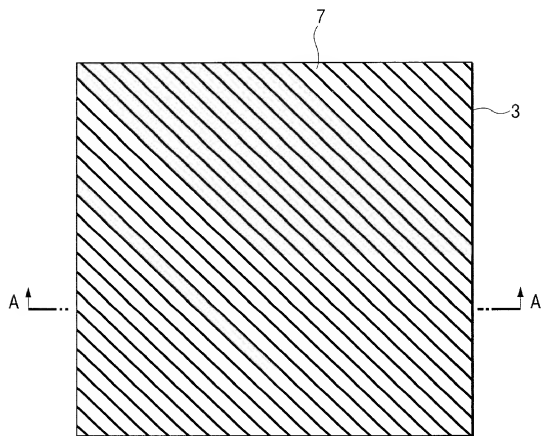


FIG. 19(b)

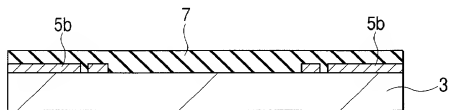


FIG. 20(a)

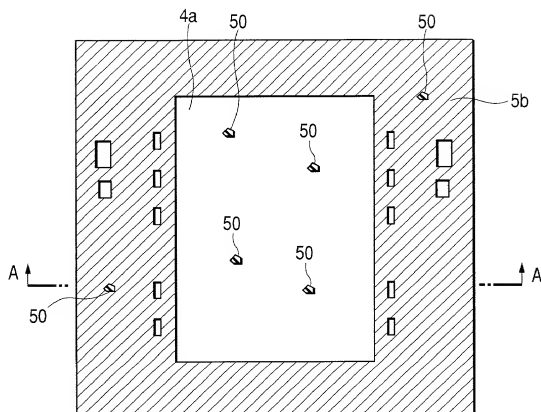


FIG. 20(b)

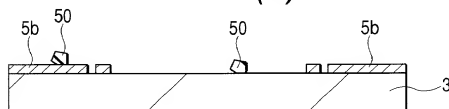


FIG. 21(a)

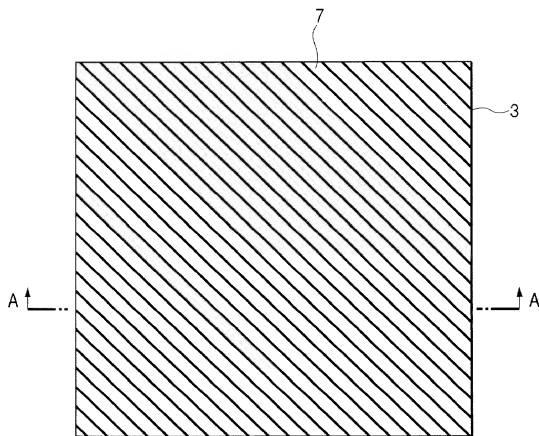


FIG. 21(b)

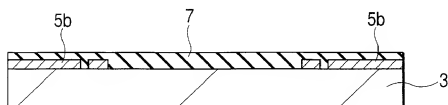


FIG. 22(a)

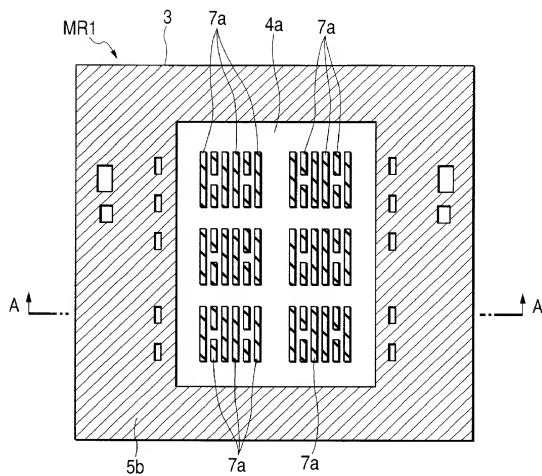


FIG. 22(b)

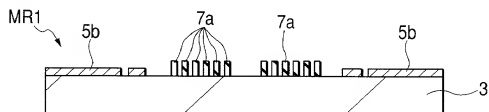


FIG. 23(a)

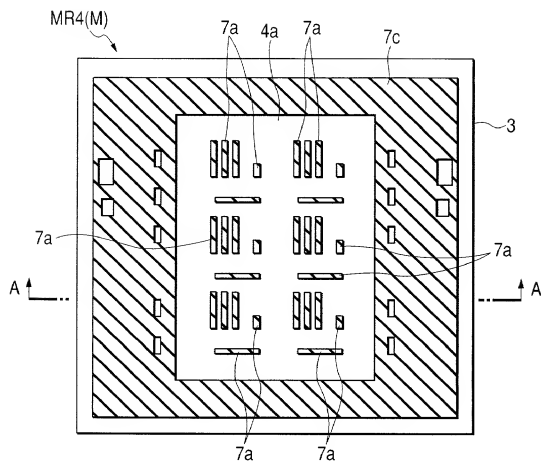


FIG. 23(b)

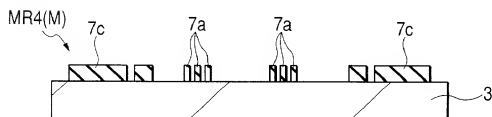


FIG. 24(a)

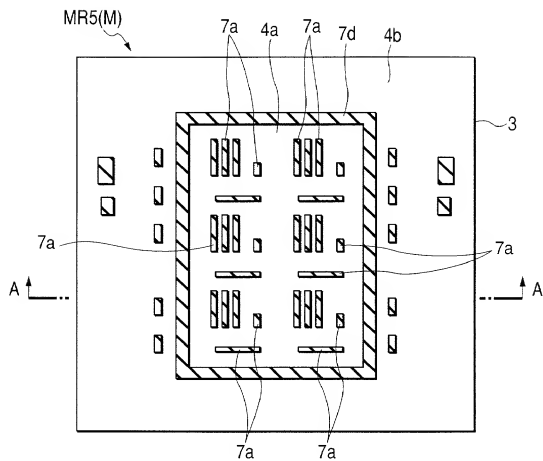


FIG. 24(b)

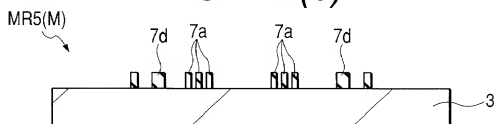




FIG. 25(a)

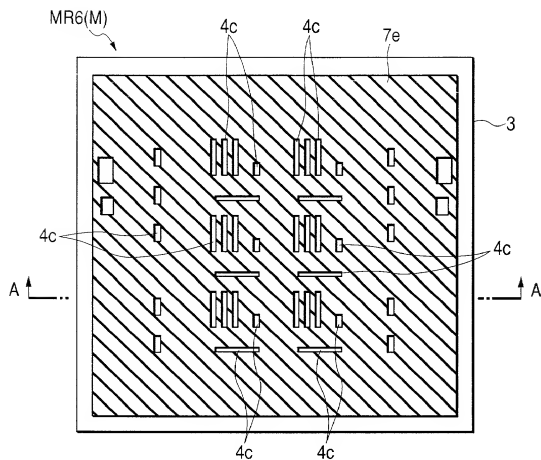
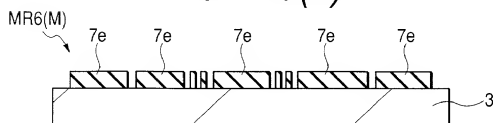


FIG. 25(b)



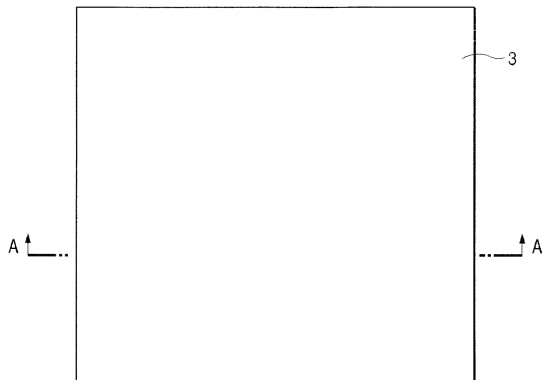
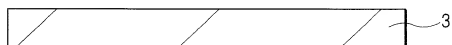
*FIG. 26(a)**FIG. 26(b)*

FIG. 27(a)

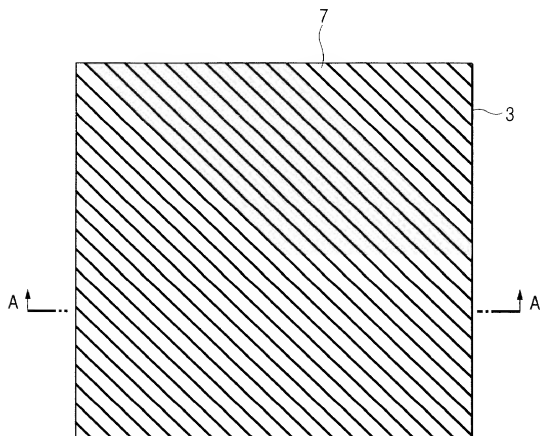


FIG. 27(b)

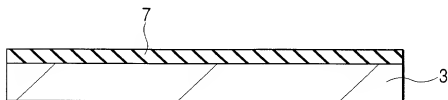


FIG. 28(a)

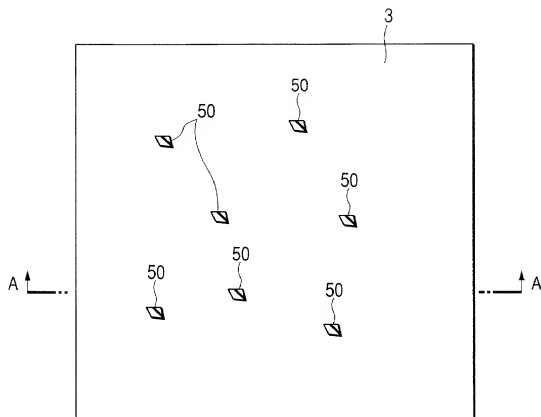
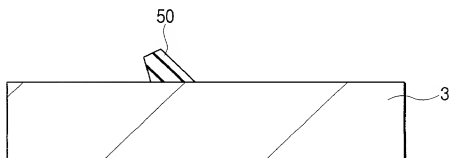
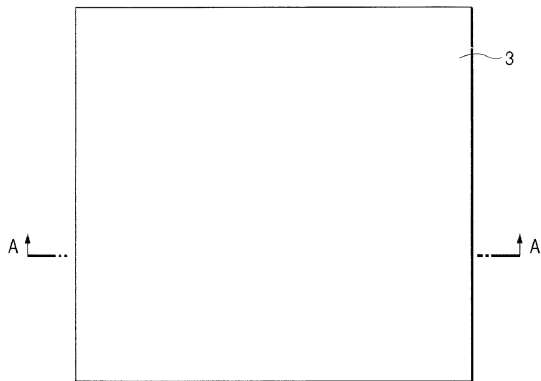


FIG. 28(b)



*FIG. 29(a)*



*FIG. 29(b)*

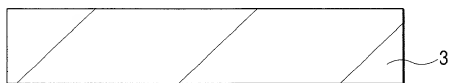


FIG. 30(a)

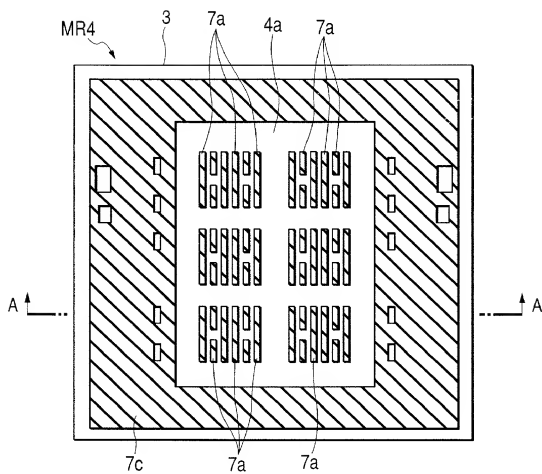


FIG. 30(b)

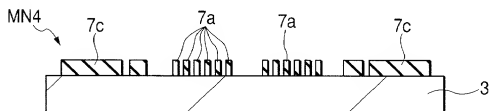


FIG. 31(a)

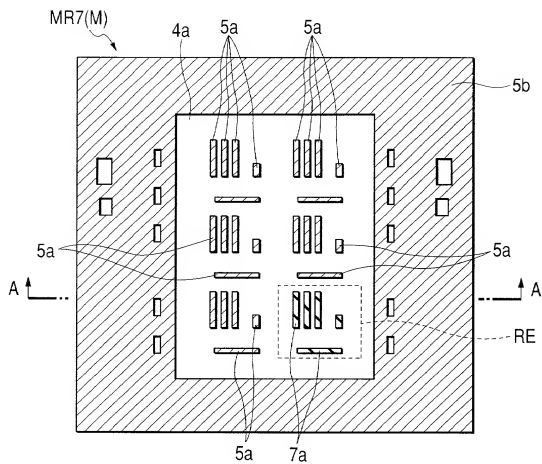


FIG. 31(b)

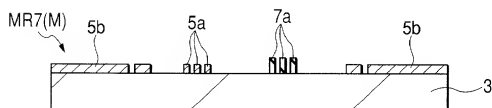






FIG. 33(a)

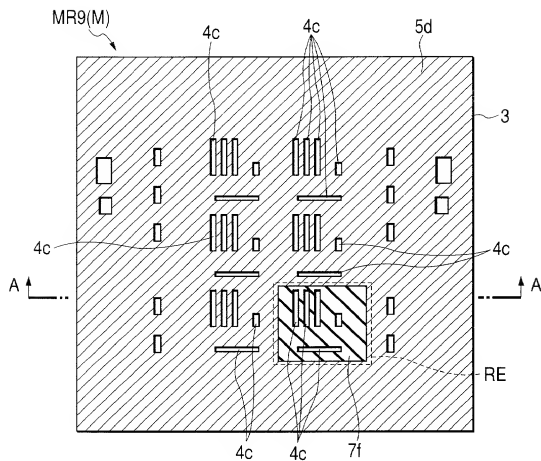
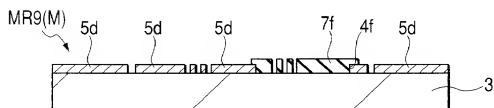


FIG. 33(b)



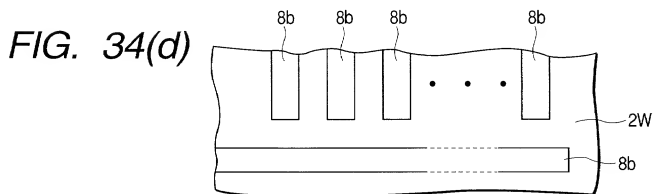
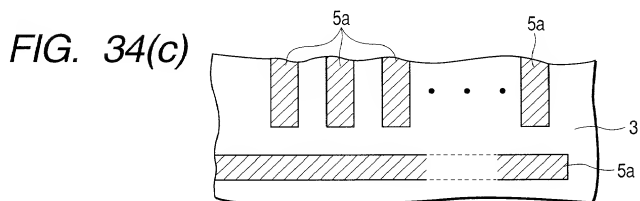
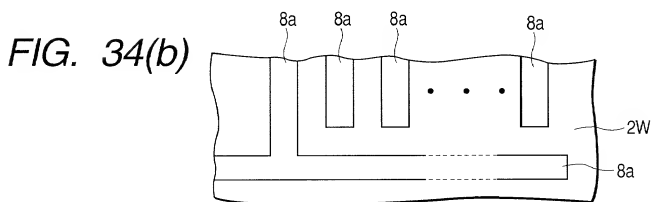
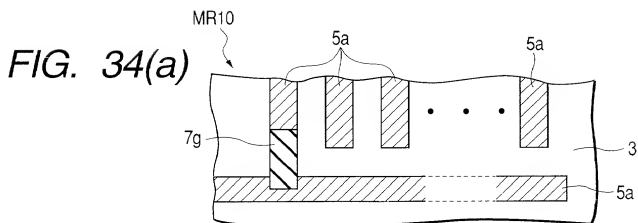


FIG. 35(a)

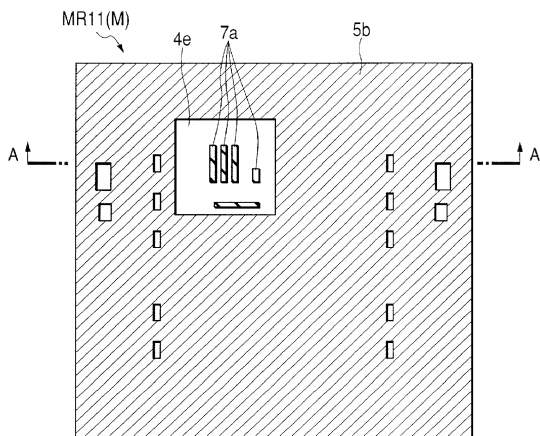


FIG. 35(b)

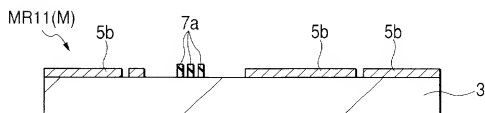


FIG. 36(a)

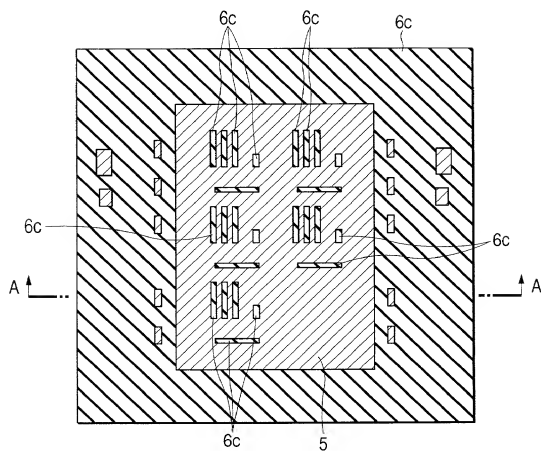


FIG. 36(b)

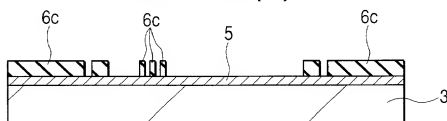


FIG. 37(a)

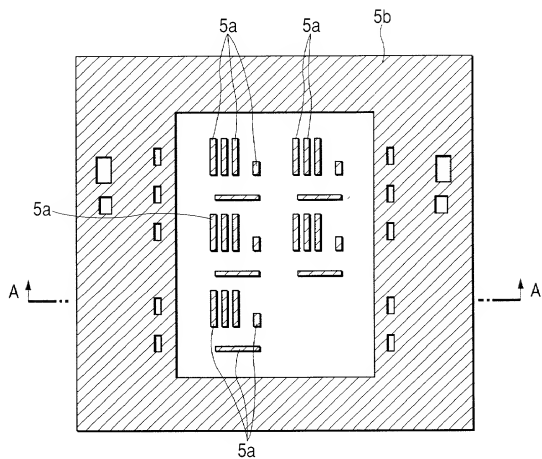


FIG. 37(b)



FIG. 38(a)

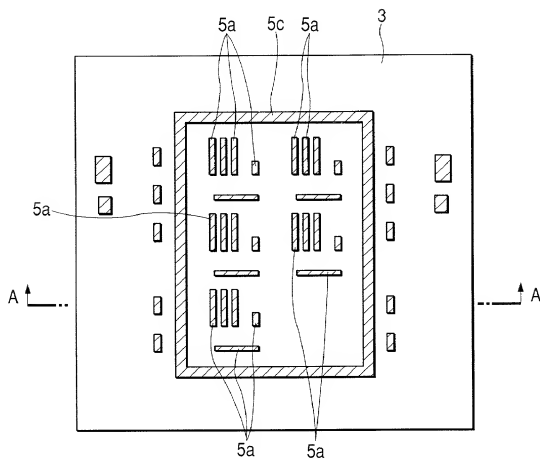


FIG. 38(b)

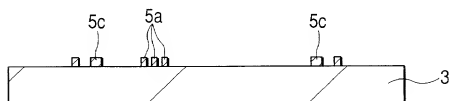


FIG. 39(a)

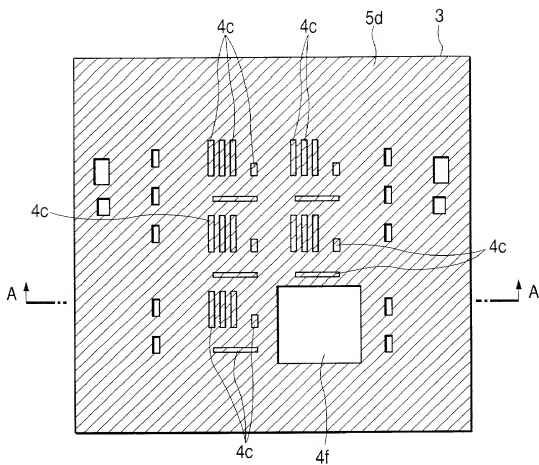


FIG. 39(b)

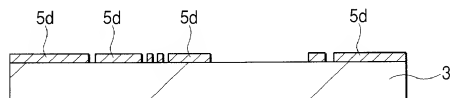


FIG. 40(a)

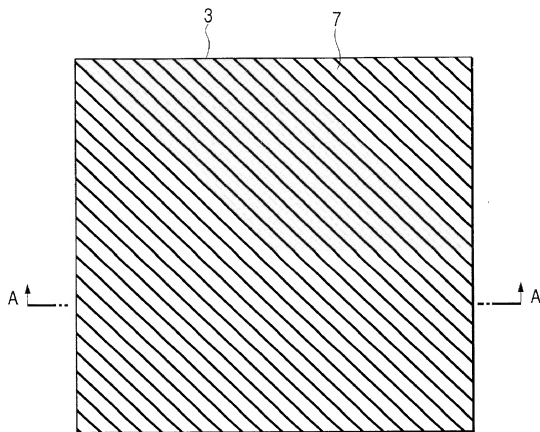


FIG. 40(b)

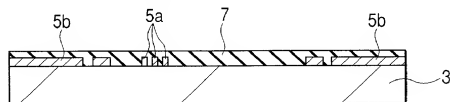




FIG. 41(a)

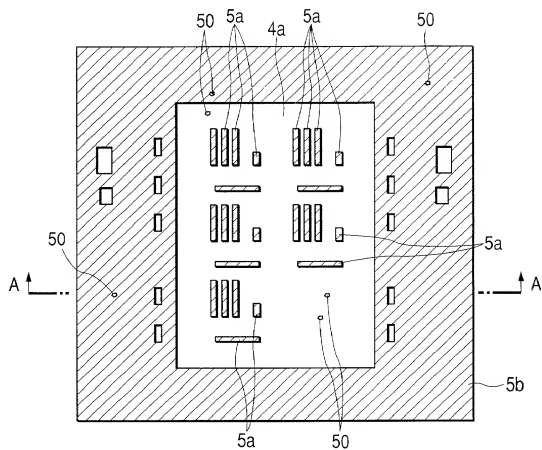


FIG. 41(b)

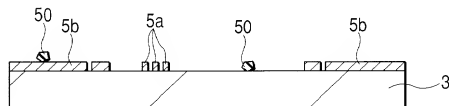


FIG. 42(a)

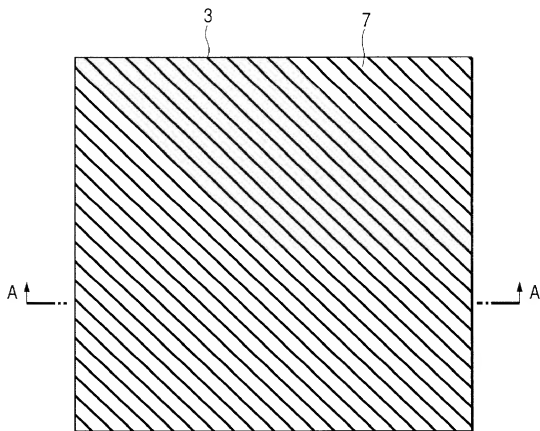


FIG. 42(b)

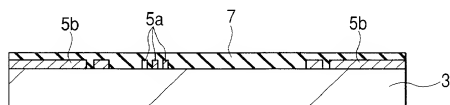


FIG. 43(a)

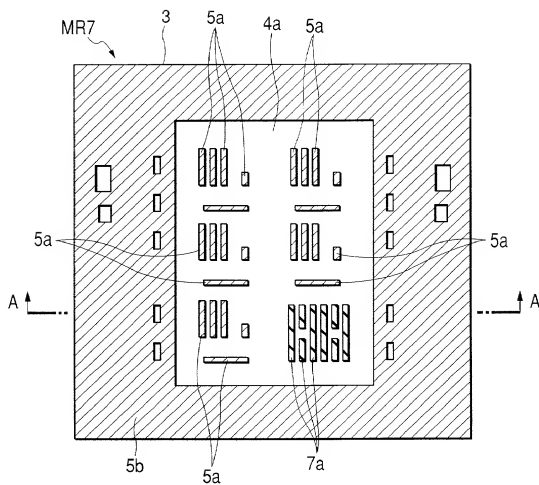
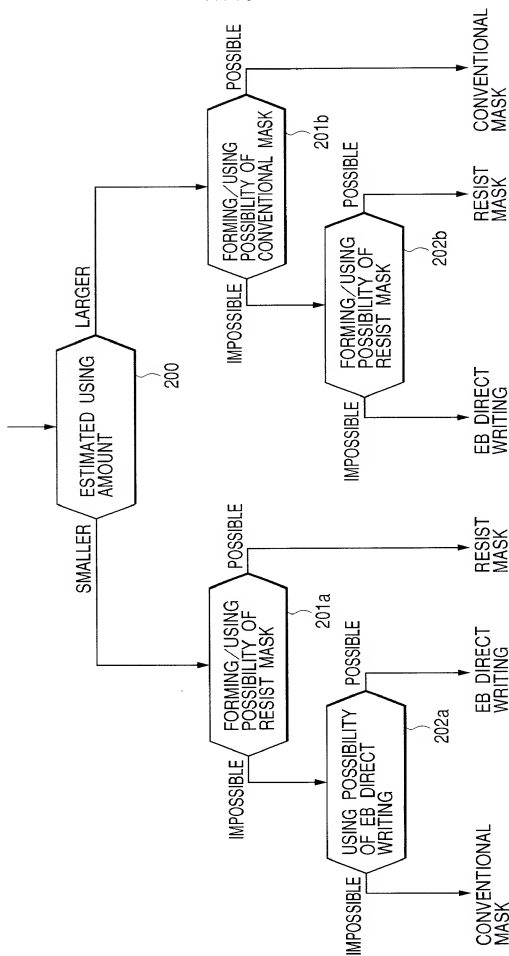


FIG. 43(b)



FIG. 44



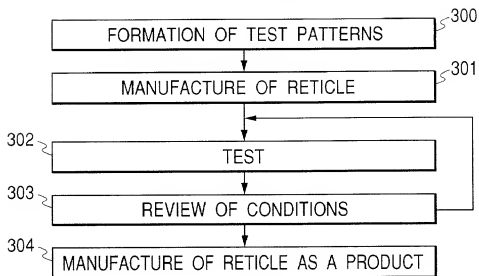
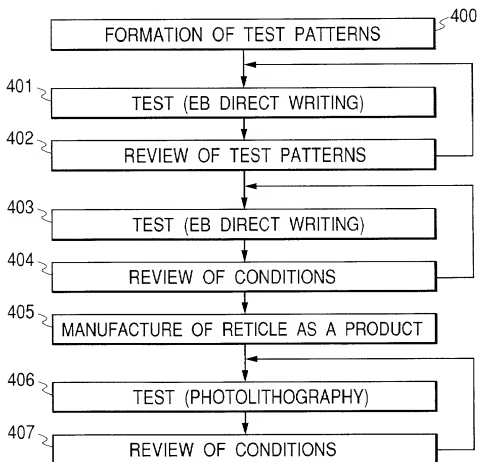
**FIG. 45****FIG. 46**

FIG. 47

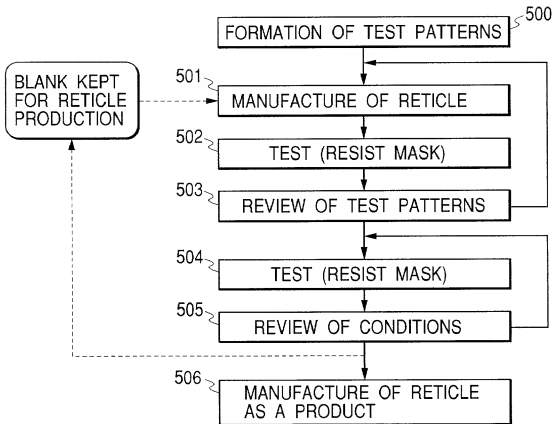


FIG. 48

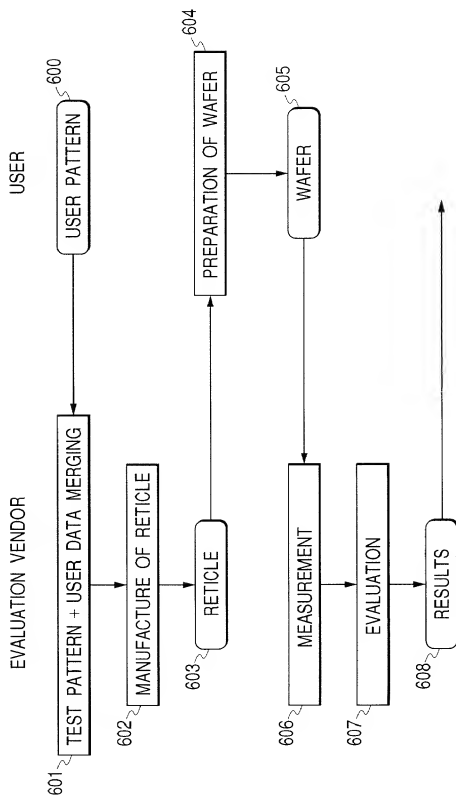
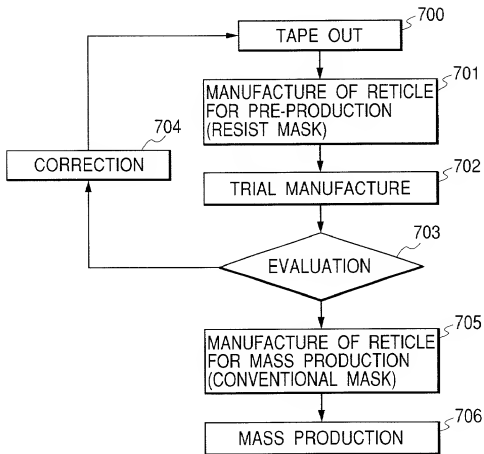


FIG. 49





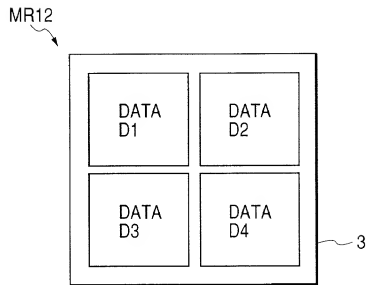
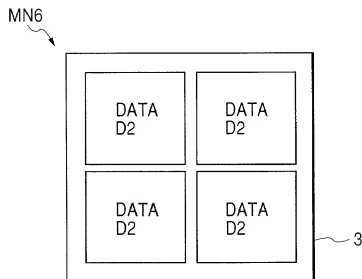
*FIG. 50(a)**FIG. 50(b)*

FIG. 51(a)

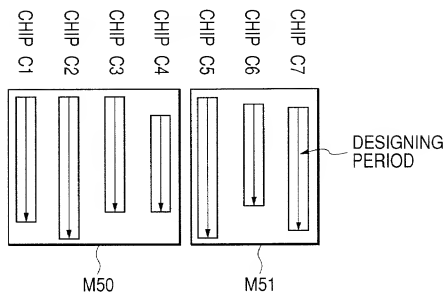


FIG. 51(b)

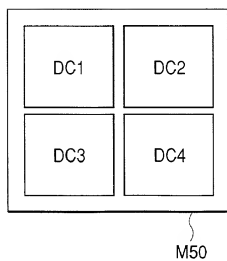


FIG. 51(c)

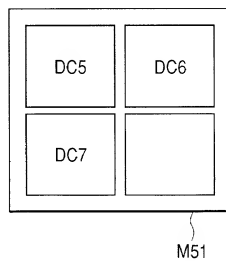


FIG. 52(a)

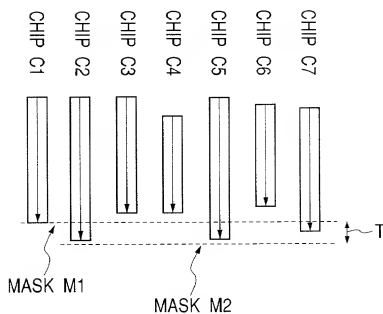


FIG. 52(b)

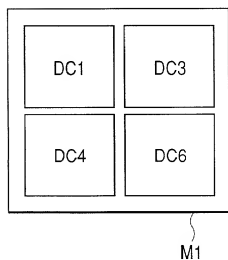
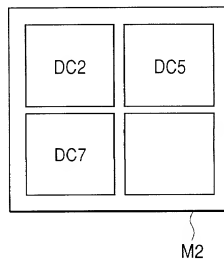


FIG. 52(c)



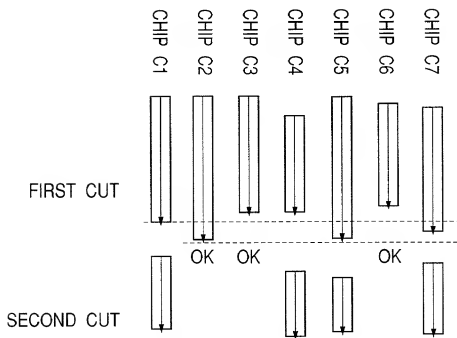
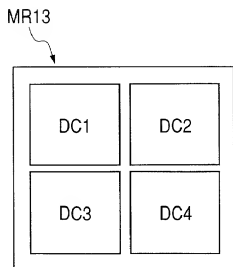
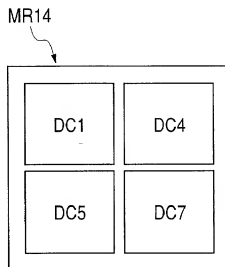
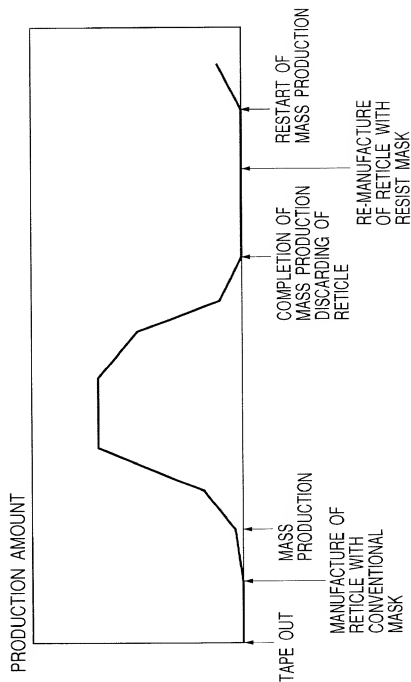
*FIG. 53(a)**FIG. 53(b)**FIG. 53(c)*

FIG. 54



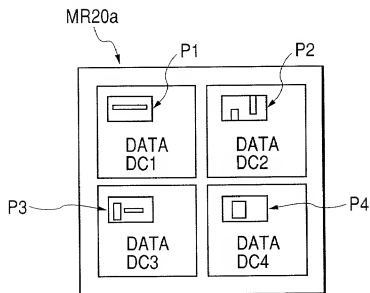
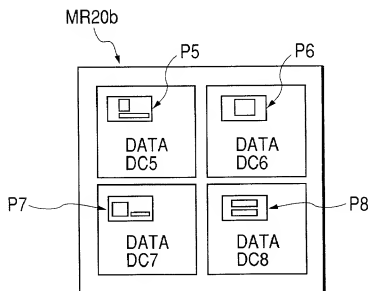
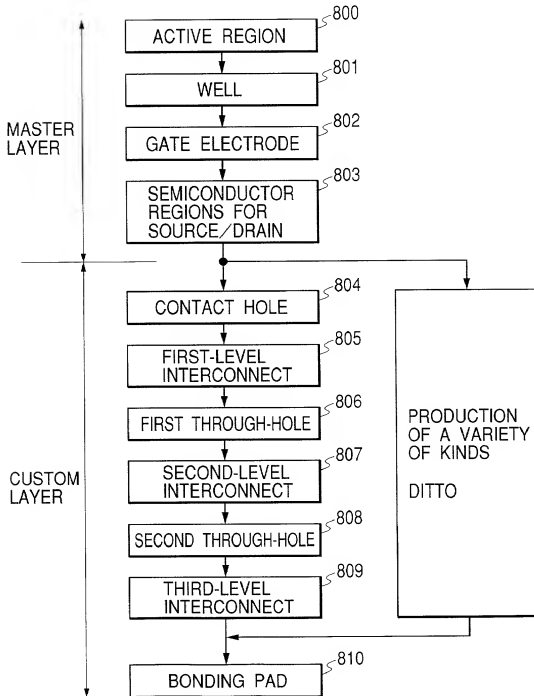
*FIG. 55(a)**FIG. 55(b)*

FIG. 56



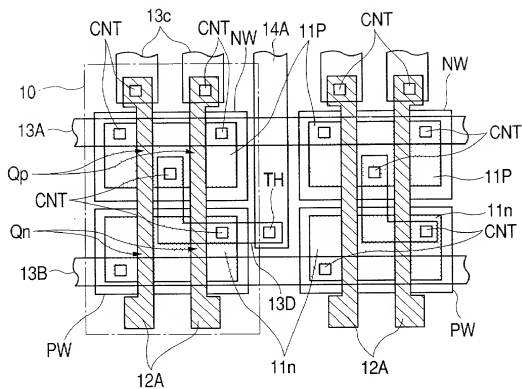
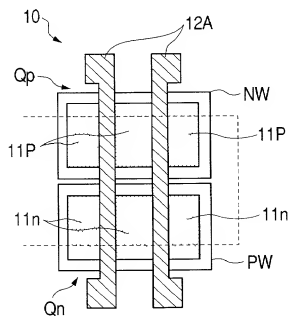
**FIG. 57****FIG. 58**



FIG. 59(a)

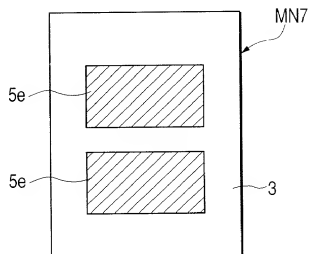


FIG. 59(b)

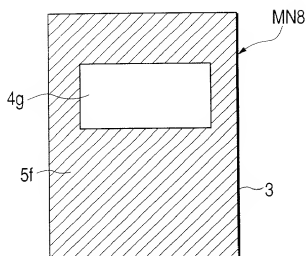


FIG. 59(c)

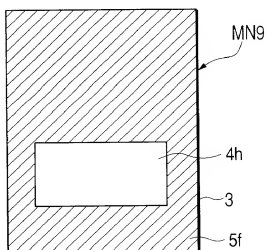


FIG. 59(d)

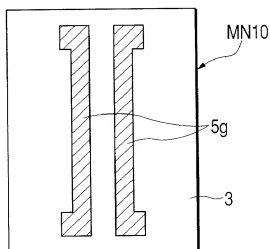


FIG. 60

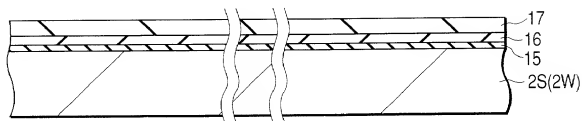


FIG. 61

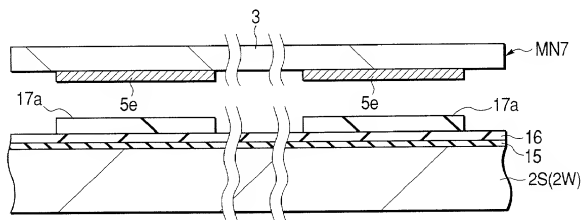


FIG. 62

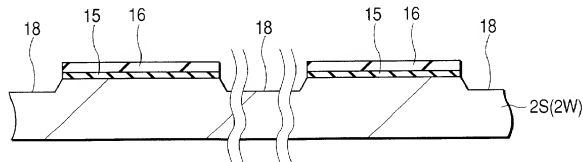


FIG. 63

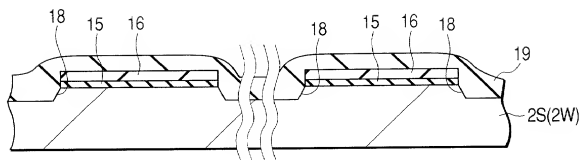


FIG. 64

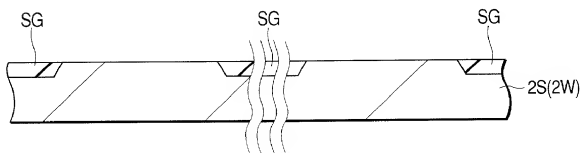


FIG. 65

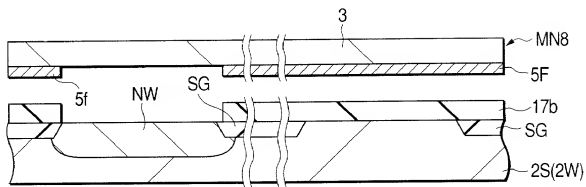


FIG. 66

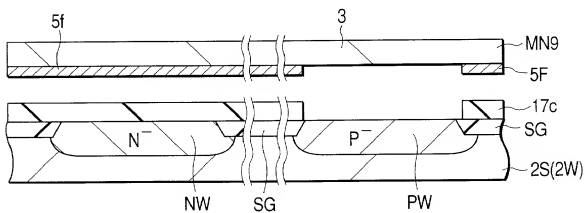


FIG. 67

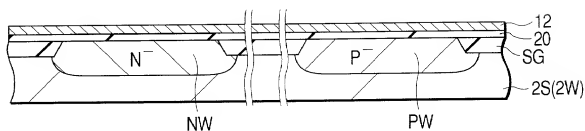


FIG. 68

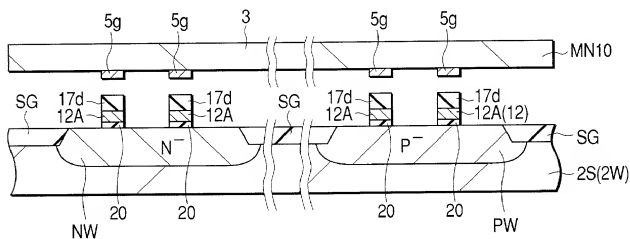


FIG. 69

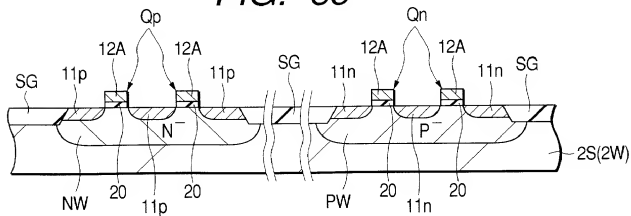


FIG. 70(a)

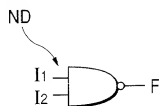


FIG. 70(b)

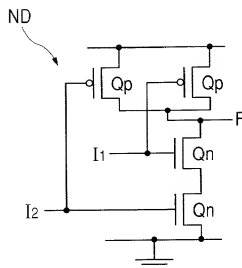


FIG. 70(c)

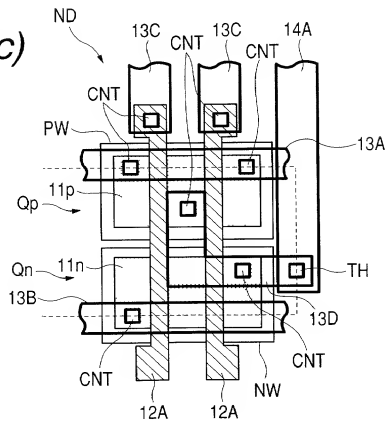


FIG. 71(a)

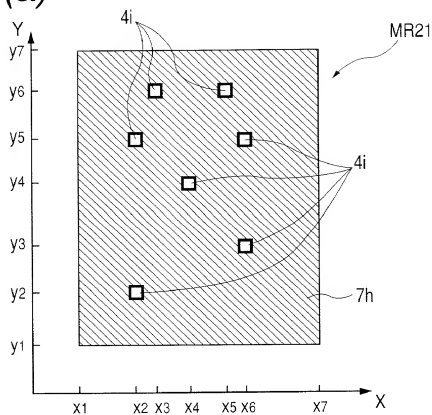


FIG. 71(b)

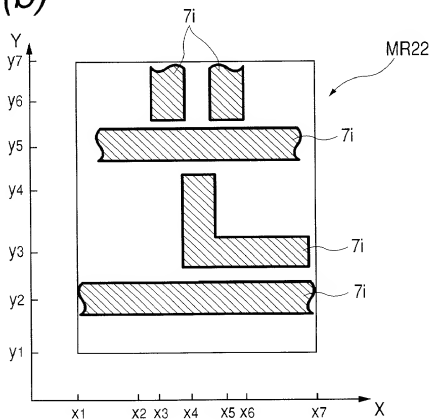


FIG. 72

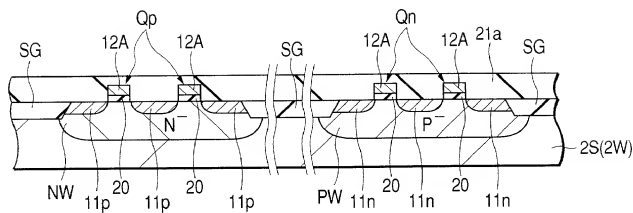


FIG. 73

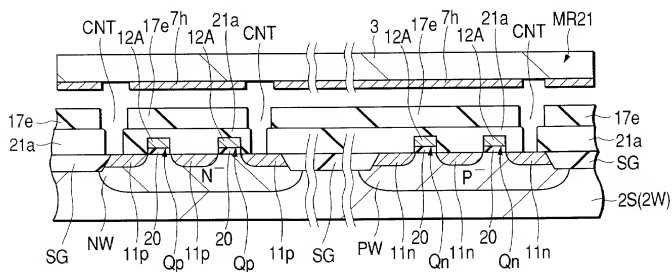




FIG. 74

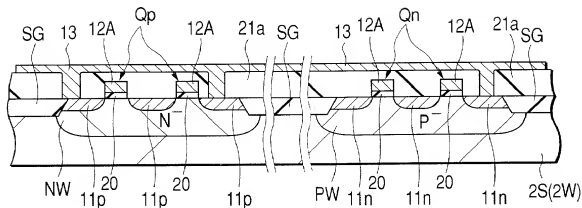


FIG. 75

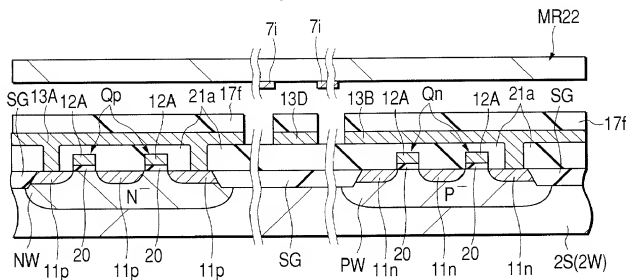


FIG. 76

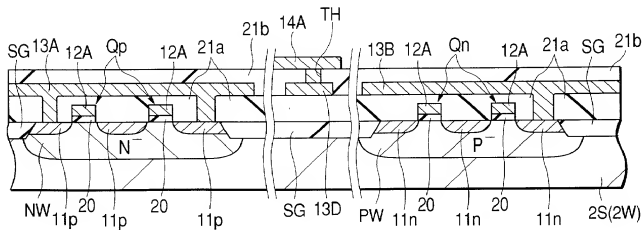


FIG. 77(a)

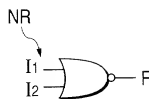


FIG. 77(b)

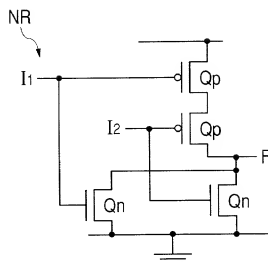


FIG. 77(c)

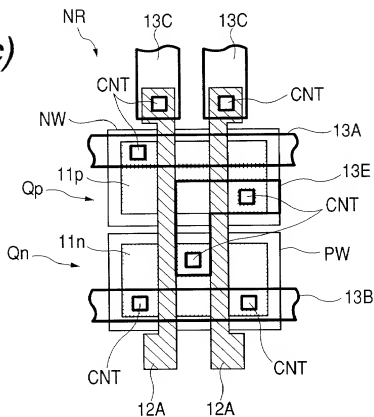


FIG. 78(a)

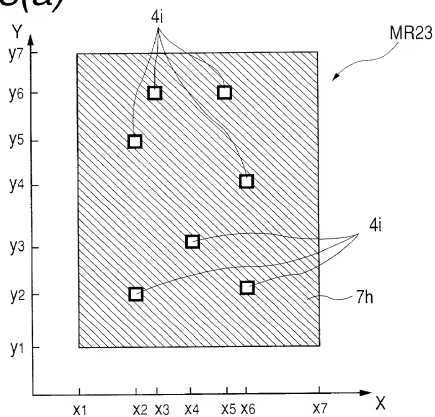


FIG. 78(b)

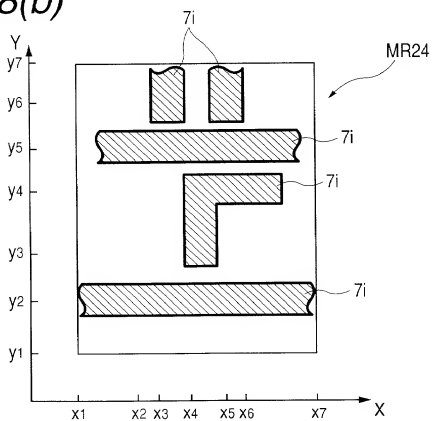


FIG. 79

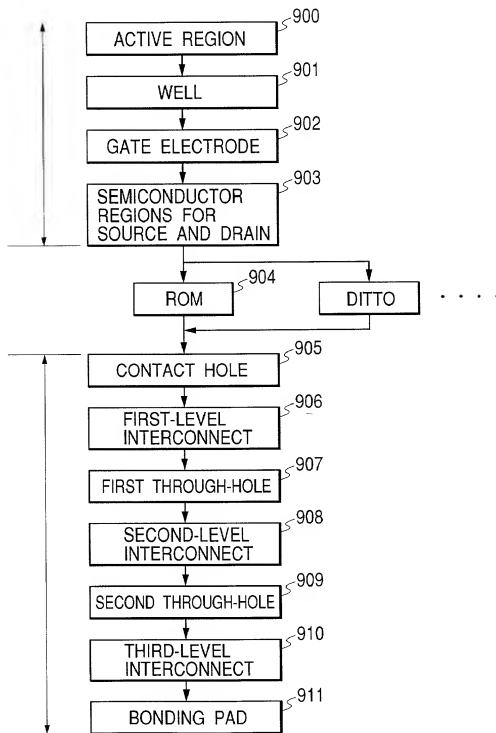


FIG. 80(a)

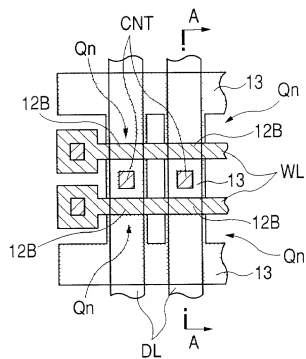


FIG. 80(b)

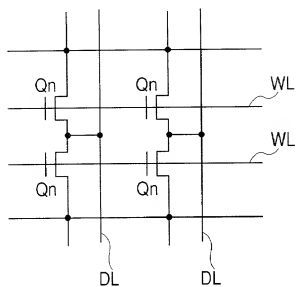


FIG. 80(c)

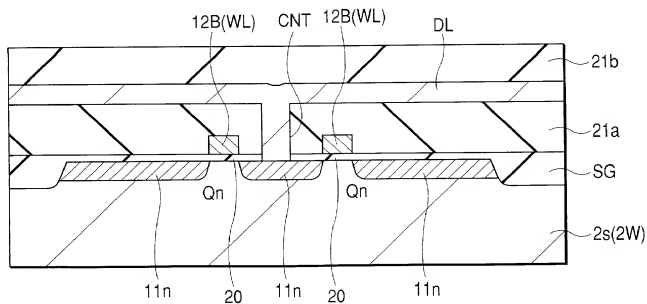


FIG. 81(a)

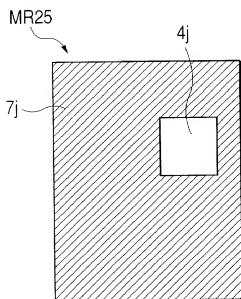


FIG. 81(b)

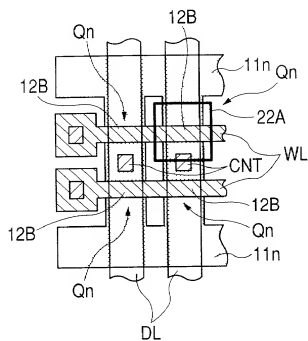
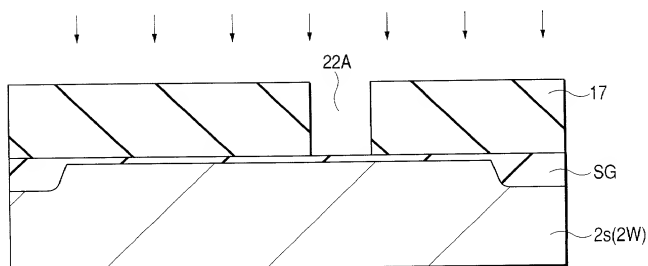


FIG. 81(c)



This diagram shows a cross-sectional view of a semiconductor device. It features a grid of word lines (WL) and bit lines (DL). A central access transistor structure is formed by a gate stack (12B) and a channel region (11n). The structure is surrounded by a gate oxide layer (12B) and a gate electrode (12B). The device is formed on a substrate (11n) and includes a gate oxide layer (12B) and a gate electrode (12B). The labels include CNT, Qn, 12B, 11n, 22C, WL, 12B, 11n, Qn, and DL.

Diagram illustrating a cross-sectional view of a semiconductor device. The device includes a substrate 2s(2W) with a layer 17h and a gap 22C. A layer SG is on the surface, and arrows indicate light incident from above.





FIG. 84(a)

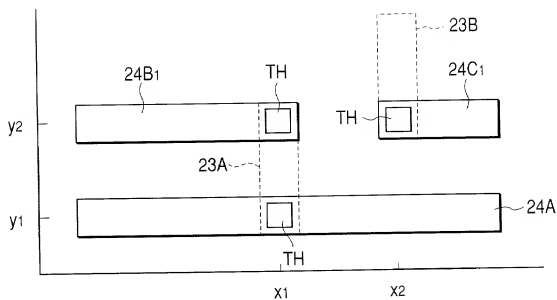


FIG. 84(b)

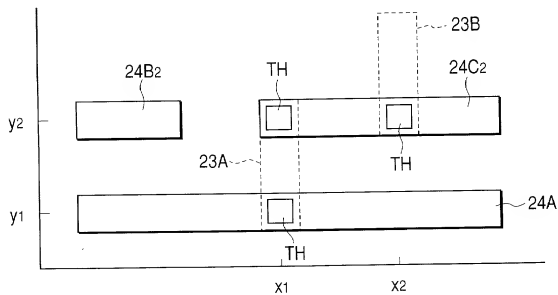


FIG. 85(a)

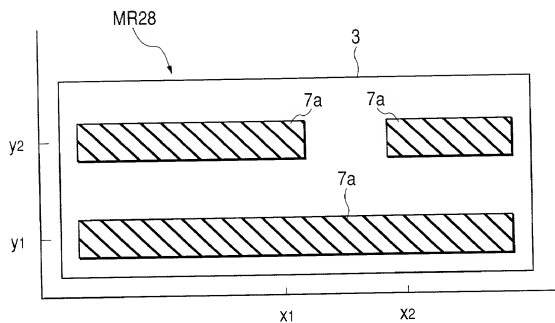


FIG. 85(b)

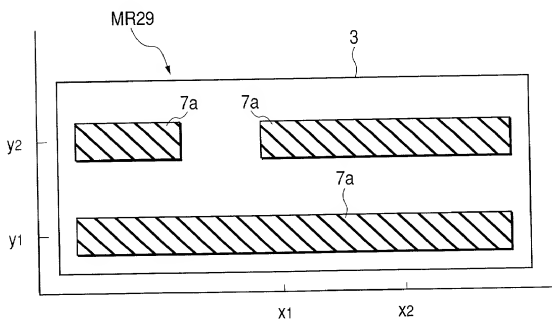


FIG. 86

